

## Electronic Supplementary Information

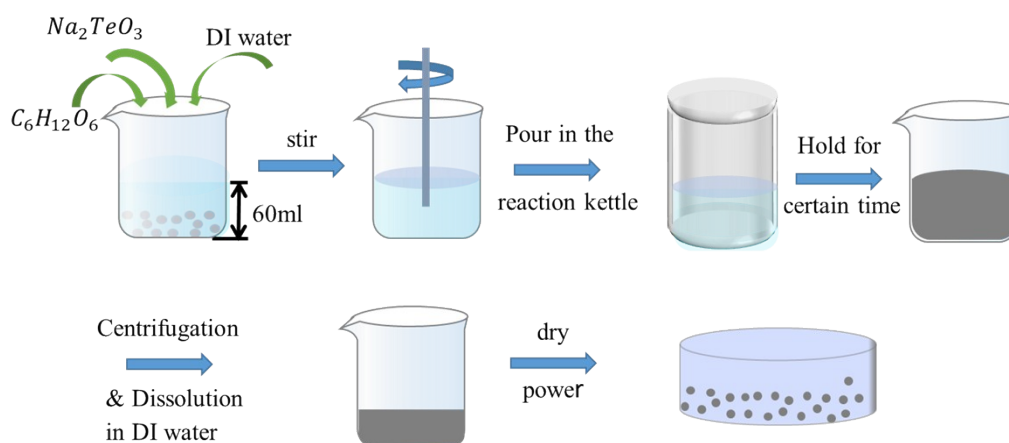
### Morphology-controlled green synthesis of Tellurium Nanostructures and application of Te/MXene hybrid structure

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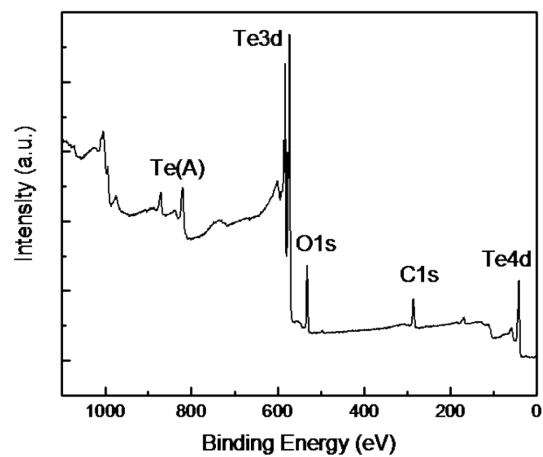
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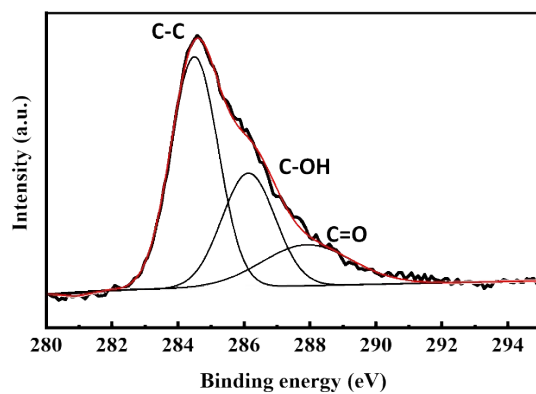
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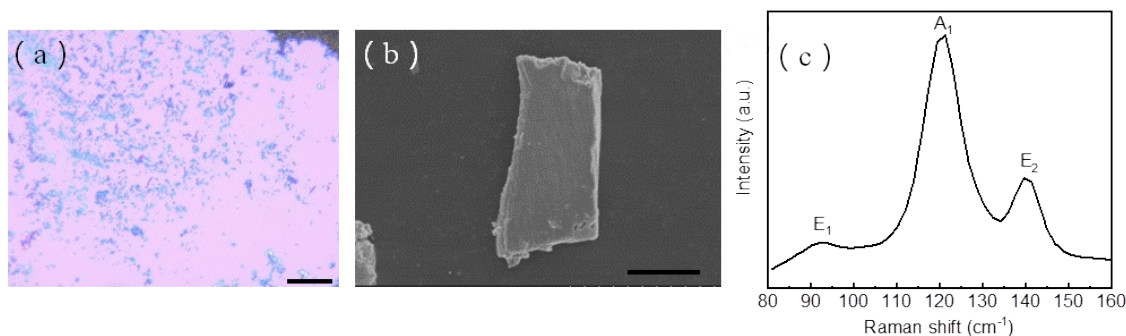
**Figure S1.** Experimental method and operation process of synthesizing Te NWs



**Figure S2.** Wide-range XPS spectra of Te nanotube prepared at 90 °C. Obvious Te 3d peaks are demonstrated by the XPS spectra of Te nanotubes, similar to those of Te nanowires.

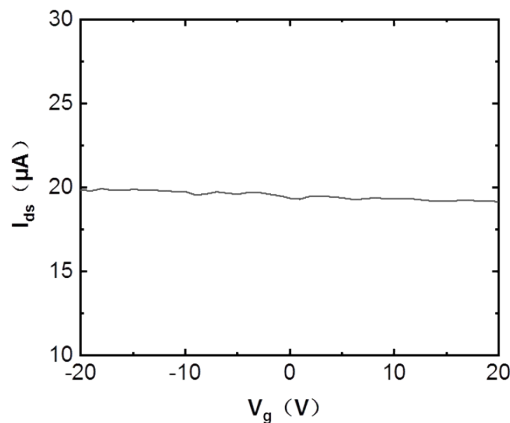


**Figure S3.** High-resolution XPS spectrum of the C 1s peak for Te/C nanocables.



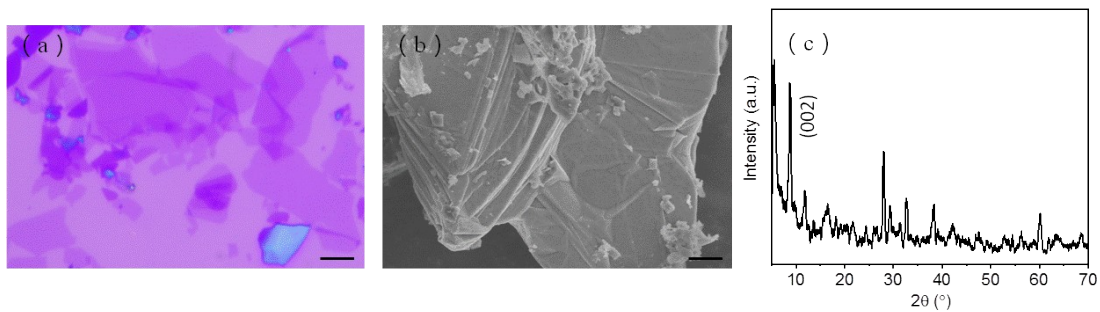
**Figure S4.** (a) OM image of the synthesized tellurene on SiO<sub>2</sub> substrate. Scale bar, 30  $\mu\text{m}$ . (b) SEM image of synthesized tellurene. Scale bar, 5  $\mu\text{m}$ . (c) Raman spectra of the synthesized tellurene.

The images in Figure S4 exhibit the characterizations of the synthesized 2D tellurene. Figure S4a is the OM image of tellurene on a SiO<sub>2</sub> substrate, in which various uniform 2D nanosheets were observed. The SEM image in Figure S4b confirms the lateral dimension of tellurene  $\sim 10 \mu\text{m}$ . Raman spectroscopy was used to explore the crystal structure of the obtained tellurene, and the spectra are shown in Figure S4c. Three active modes located at 92, 121, and 141  $\text{cm}^{-1}$  are donated as the E1, A1, and E2 vibration modes, respectively, consistent with the reported works.<sup>1-3</sup>



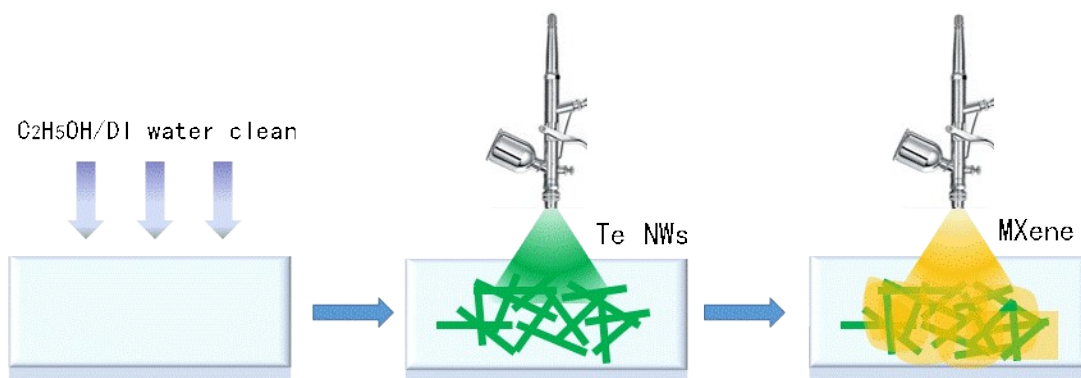
**Figure S5.** Transfer curve of the synthesized Te NWs film.  $V_d=0.1 \text{ V}$ .

For the transfer curve in Figure S5, the drain current slightly changed with the increase of gate voltage from -20 V to 20 V, and high drain current could be obtained at low drain voltage, indicating the high metallic conductivity of Te NWs. As reported, high junction resistance exists between individuals in nanotube films<sup>4</sup> and the poorly conductive amorphous carbon shells of nanocables decrease the conductivity of Te nanocable film<sup>5</sup>, so Te NWs were employed for the application of transparent conductive electrodes in this work.



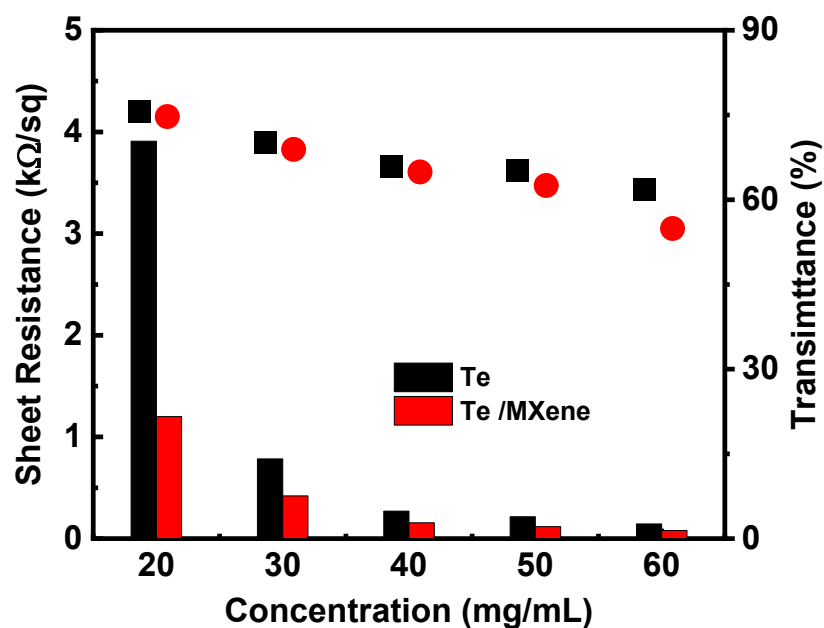
**Figure S6.** (a) OM image of the synthesized  $\text{Ti}_3\text{C}_2\text{T}_x$  flakes on  $\text{SiO}_2$  substrate. Scale bar, 2  $\mu\text{m}$ . (b) SEM images of synthesized tellurene. Scale bar, 2  $\mu\text{m}$ . (c) XRD pattern of the synthesized  $\text{Ti}_3\text{C}_2\text{T}_x$ .

The investigations of the synthesized  $\text{Ti}_3\text{C}_2\text{T}_x$  flakes are shown in Figure S6. The OM image in Figure S6a and SEM image in Figure S6b indicate the exfoliated large-area and thin  $\text{Ti}_3\text{C}_2\text{T}_x$  flakes. The XRD pattern in Figure S6c further confirms the high quality of the achieved  $\text{Ti}_3\text{C}_2\text{T}_x$  flakes, in which a weak peak at  $39^\circ$  is observed.<sup>6,7</sup>



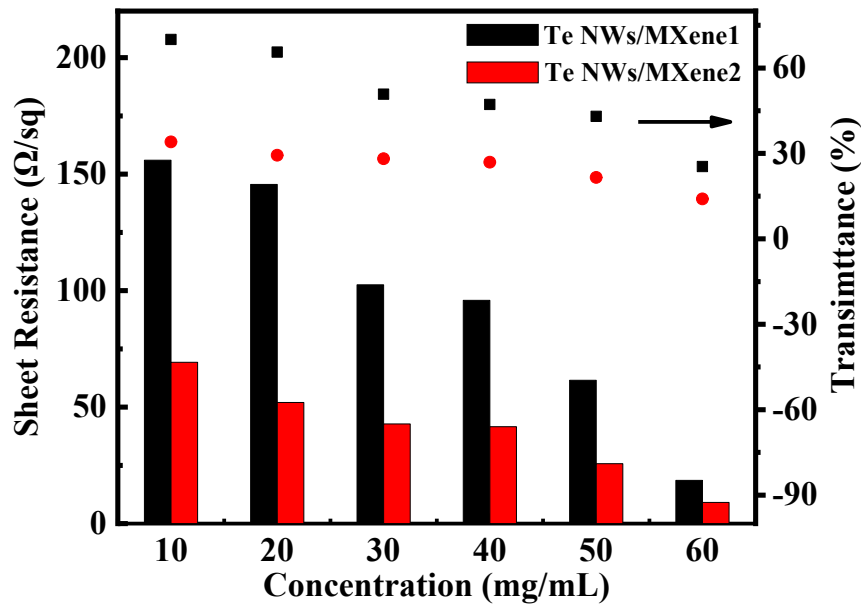
**Figure S7.** Schematic of the fabrication process of Te NWs/MXene hybrid structures.

Figure S7 is the schematic of fabricating Te NWs/MXene hybrid structure. Firstly, the substrate was cleaned with ethanol ( $\text{C}_2\text{H}_5\text{OH}$ ) and deionized (DI) water. Then, in sequence, Te NWs and MXene solutions were spray-coated on the prepared substrate.



**Figure S8.** Sheet resistances and transmittances of Te and Te NWs/MXene hybrid structures with different solution concentrations of Te NWs.

The sheet resistances and transmittances at 550 nm of pure Te and Te NWs/MXene hybrid structures were measured and summarized in Fig. S8. With the spray-coating of the MXene layer, significant performance enhancements were demonstrated by Te/MXene hybrid structures with lower sheet resistances and similar transmittances. When the solution concentration of Te NWs is 10 mg/mL, the sheet resistance of Te film is difficult to measure, so 20 mg/mL is the minimum concentration investigated in this work.



**Figure S9.** Sheet resistances and transmittances of Te NWs/MXene hybrid structure with different solution concentrations of MXene. Te NWs/MXene1: Te NWs/MXene hybrid structure with one layer of MXene. Te NWs/MXene2: Te NWs/MXene hybrid structure with two layers of MXene.

**Table S1** A comparison of various transparent conductive electrodes.

Material	Method	Sheet resistance (Ω/sq)	Transmittance (%)	Refs.
Ti <sub>3</sub> C <sub>2</sub> T <sub>x</sub> in water	Spray-coating	1300	68	8
Ti <sub>3</sub> C <sub>2</sub> T <sub>x</sub> in ethanol	Spray-coating	3500	58	8
rGO	Filtration	565	59	9
graphene	CVD growth	280	80	10
Te/MXene	Spray-coating	156	70	This work

rGO: reduced graphene oxide.

Various transparent conductive electrodes based on nanomaterials are summarized in Table 1. Compared with pure Ti<sub>3</sub>C<sub>2</sub>T<sub>x</sub> TCEs, the Te/MXene hybrid structure shows a lower sheet resistance with a higher transmittance, which is supposed to be attributed to (1) the Te NWs distributed across the MXene flakes act as conductive bridges and reduce the contact resistance.<sup>11</sup> (2) the Te/MXene hybrid structure could be a resistivity in parallel problems, the total resistance of Te/MXene TCE is lower than every individual component in the hybrid conductive structures.<sup>12</sup> Therefore, compared to pure MXene film, Te/MXene hybrid TCE demonstrates a better performance.

## References

1. Y. H. Jianting Lu, Churong Ma, Qiaojue Ye, Huaxin Yi, Zhaoqiang Zheng, and a. G. Y. Jiandong Yao, *Adv. Mater.*, 2023, **35**, 2211562.
2. G. Q. Yixiu Wang, Ruoxing Wang, Shouyuan Huang, Qingxiao Wang, Yuanyue Liu,, W. A. G. I. Yuchen Du, Moon J. Kim, Xianfan Xu, Peide D. Ye and and W. Wu, *Nature Electronics*, 2018, **1**, 228-236.
3. G. Liu, J. Yuan, T. Wu, F. Zhang, F. Xing, W. Zhang, H. Zhang and S. Fu, *IEEE J. Sel. Top. Quantum Electron.*, 2021, **27**, 1-6.
4. P. J. K. Sukanta De, Philip E. Lyons, Umar Khan, and Jonathan N. Coleman, *ACS nano*, 2010, **4**, 7064–7072.
5. W. X. a. S.-H. Yu, *Small*, 2009, **5**, 460–465.
6. H. Y. Shunlong Zhang, Pengfei Huang, Jianli Wang, Zhao Zhang, Tiantian Yang, and Wei-Qiang Han, *ACS nano*, 2020, **14**, 17665-17674.
7. H. L. Wanlin Feng, Yu Wang, Sifan Zeng, Lianwen Deng, Xiaosong Zhou, Haibin Zhang and Shuming Peng, *RSC Adv.*, 2018, **8**, 2398.
8. M.-Q. Z. Kanit Hantanasirisakul , Patrick Urbankowski , Joseph Halim , Babak Anasori , Sankalp Kota , Chang E. Ren , Michel W. Barsoum , and Yury Gogotsi *Adv. Electron. Mater.*, 2016, **2**, 1600050.
9. C. P. Dimitrios Konios , George Kakavelakis , Maria Sygletou , Kyriaki Savva , Emmanuel Stratakis , \* and Emmanuel Kymakis *Adv. Funct. Mater.*, 2015, **25**, 2213–2221.
10. K. S. Kim, Y. Zhao, H. Jang, S. Y. Lee, J. M. Kim, K. S. Kim, J.-H. Ahn, P. Kim, J.-Y. Choi and B. H. Hong, *Nature*, 2009, **457**, 706-710.
11. J. Y. Su Ding, Fei Chen, Li Fu, Yanfei Lv, Shichao Zhao, Guoqiang Ji, *J. Nanopart. Res.*, 2021, **23**, 111.
12. W.-C. H. Tien-Chai Lin, Fu-Chun Tsai *Microelectron. Eng.*, 2017, **167**, 85–89.